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ATTY DOCKET NO. 3308 CON

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

4/3/13

*Smith*

IN THE APPLICATION OF: )

BIN-SHING CHEN )

Group Art Unit 2811

SERIAL NO.: (Continuation of 09/769,576) )

Examiner Thien F. Tran

FILED: )

FOR: METHOD FOR MANUFACTURING )  
SPLIT-GATE EEPROM MEMORY )  
CELL AND STRUCTURE FORMED )  
THEREBY )

**PRELIMINARY AMENDMENT**

The Honorable Commissioner of  
Patents and Trademarks  
Washington, D. C. 20231

Sir:

RECEIVED  
MAR 31 2003  
TECHNOLOGY CENTER 2800

This application is a continuation application of prior application U.S. Serial No. 09/769,586

**In the Claims:**

Please cancel claims 1-10, amend Claim 11, and add new Claim 12 as follows:

*SUB C17* 11. (Once Amended) A structure of an Electrically Erasable Programmable Read-Only  
Memory (EEPROM), comprising:

*B1* a silicon substrate *C* having a source/drain region;

a tunnel oxide layer disposed over said silicone substrate;

a select gate disposed over said tunnel oxide layer, wherein said select gate is defined  
by a conductive layer covered with a first insulated material thereon and comprises a sidewall made  
of a second insulated material;

a sidewall forming a single floating gate aligned to one side of said select gate;